ABSTRACT OF THE DISCLOSURE

In an embodiment of an integrated circuit structure having buried layer substrate isolation and a method for forming same, a buried layer having conductivity type opposite to that of an overlying well region is used for wells containing transistors prone to noise generation, where the wells are of the same conductivity type as the substrate. The buried layer may in some embodiments include a first portion underlying the transistor and a second portion spaced apart from and laterally surrounding the first portion. In some embodiments, the circuit may include a doped annular region of the same conductivity type as the buried layer, where the annular region contacts a portion of the buried layer and laterally surrounds the transistor. The circuit may further include metallization adapted to connect the well and annular region to opposite polarities of a power supply voltage, or in some embodiments to preclude such connection.